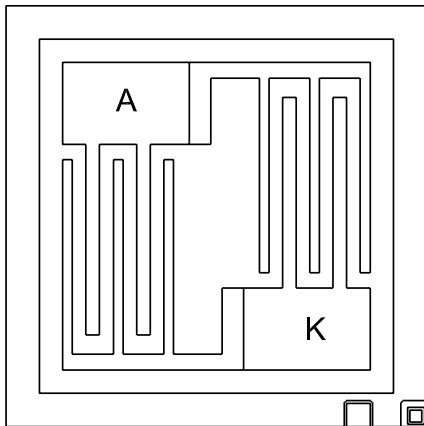


PROCESS CP622
Programmable
Unijunction Transistor

PROCESS DETAILS

Process	PLANAR PASSIVATED
Die Size	27.5 x 27.5 MILS
Die Thickness	11 MILS
Anode Bonding Pad Area	7.1 x 5.1 MILS
Cathode Bonding Pad Area	7.1 x 5.1 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 13,000Å

GEOMETRY



BACKSIDE GATE R2

GROSS DIE PER 4 INCH WAFER

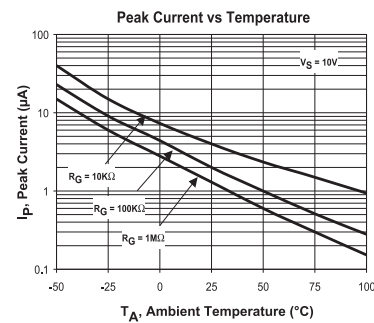
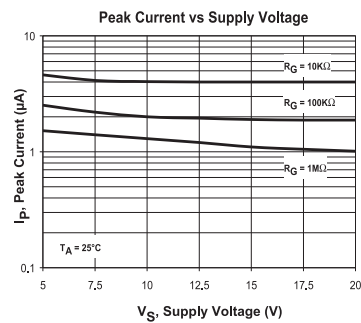
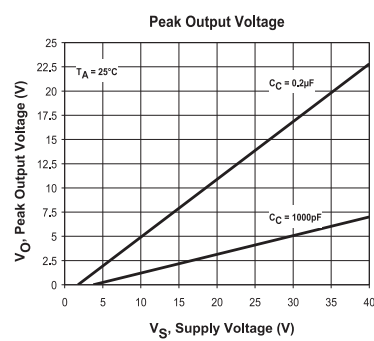
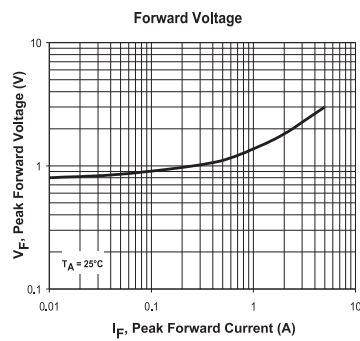
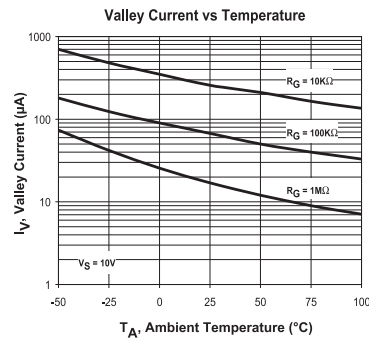
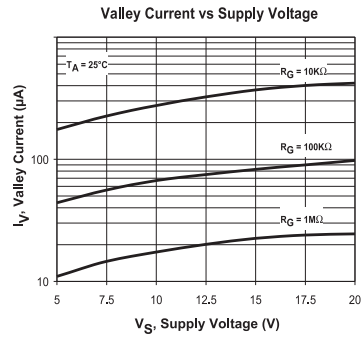
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PRINCIPAL DEVICE TYPES

2N6027

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